

TO-66 CASE



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DESCRIPTION:

The CENTRAL SEMICONDUCTOR 2N6294, 2N6296 series devices are complementary silicon Darlington power transistors, manufactured by the epitaxial base process, designed for high gain amplifier and medium speed switching applications.

MARKING: FULL PART NUMBER

MAXIMUM RA	ATINGS : (T _C =25°C) e Voltage	SYMBOL V _{CBO}	2N6294 <u>2N6296</u> 60	2N6295 <u>2N6297</u> 80	UNITS V
Collector-Emitter Voltage		VCEO	60	80	V
Emitter-Base Voltage		V _{EBO}	5.	0	V
Continuous C	ollector Current	۱ _C	4.	0	А
Peak Collecto	r Current	ICM	8.	0	А
Continuous B	ase Current	۱ _B	8	0	mA
Power Dissipa	ation	PD	5	0	W
Operating and Storage Junction Temperature		TJ, T _{stg}	-65 to	+200	°C
Thermal Resis	stance	ΘJC	3.	5	°C/W
ELECTRICAL	. CHARACTERISTICS: (T _C =25°C ur	aless otherwise	noted)		
SYMBOL	TEST CONDITIONS	MIN	MA	X	UNITS
ICEV	V _{CE} =Rated V _{CEO} , V _{EB} =1.5V		0.	5	mA
ICEV	V _{CE} =Rated V _{CEO} , V _{EB} =1.5V, T _C =	=150°C	5.	0	mA
ICEO	V _{CE} =½Rated V _{CEO}		0.	5	mA
IEBO	V _{EB} =5.0V		2.	0	mA
BVCEO	I _C =50mA, (2N6294, 2N6296)	60			V
BVCEO	I _C =50mA, (2N6295, 2N6297)	80			V
V _{CE(SAT)}	I _C =2.0A, I _B =8.0mA		2.	0	V
V _{CE(SAT)}	I _C =4.0A, I _B =40mA		3.	0	V
V _{BE(SAT)}	I _C =4.0A, I _B =40mA		4.	0	V
V _{BE(ON)}	V _{CE} =3.0V, I _C =2.0A		2.	8	V
hFE	V _{CE} =3.0V, I _C =2.0A	750	18	K	
h _{FE}	V _{CE} =3.0V, I _C =4.0A	100			
h _{fe}	V _{CE} =3.0V, I _C =1.5A, f=1.0kHz	300			
fT	V_{CE} =3.0V, I _C =1.5A, f=1.0MHz	4.0			MHz
Cob	V_{CB} =10V, I _E =0, f=100kHz (NPN type)	pes)	12	20	pF
Cob	V_{CB} =10V, I _E =0, f=100kHz (PNP type)	oes)	20	00	pF

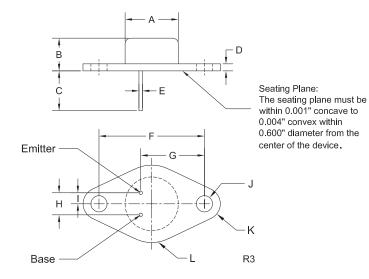
R2 (2-September 2014)



2N6294 2N6295 NPN 2N6296 2N6297 PNP

COMPLEMENTARY SILICON DARLINGTON POWER TRANSISTORS

TO-66 CASE - MECHANICAL OUTLINE



DIMENSIONS							
	INCHES		MILLIMETERS				
SYMBOL	MIN	MAX	MIN	MAX			
A (DIA)	0.470	0.500	11.94	12.70			
В	0.250	0.340	6.35	8.64			
С	0.360	-	9.14	-			
D	0.050	0.075	1.27	1.91			
E (DIA)	0.028	0.034	0.71	0.86			
F	0.956	0.964	24.28	24.48			
G	0.570	0.590	14.48	14.99			
Н	0.190	0.210	4.83	5.33			
I	0.093	0.107	2.36	2.72			
J (DIA)	0.142	0.152	3.61	3.86			
K (RAD)	0.141		3.58				
L (RAD)	0.345		8.76				
TO-66 (REV:R3)							

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